Electronic Supplementary Information

Exploration of Strain and Thermoelectric properties of hexagonal SiX (X = N, P, As, Sb, and Bi) monolayers

Radha N Somaiya¹, Yogesh Sonvane¹, and Sanjeev K. Gupta²

¹Advanced Materials Lab, Department of Applied Physics, S.V. National Institute of Technology, Surat 395007, India

²Computational Materials and Nanoscience Group, Department of Physics, St. Xavier's College, Ahmedabad 380009, India
Fig. S1 Energy shift of VBM and CBM for monolayers (a) SiN, (b) SiP, (c) SiAs, (d) SiSb, and (e) SiBi w.r.t. compressive and tensile strains.
Fig. S2 Strain energy difference between the total energy of relaxed and applied biaxial strained monolayers (a) SiN, (b) SiP, (c) SiAs, (d) SiSb, and (e) SiBi w.r.t. compressive and tensile strains.
Fig. S3 Electronic band structures (a) SiN, (b) SiP, (c) SiAs, (d) SiSb, and (e) SiBi on application of compressive and tensile strain. The Fermi level is set at zero. The black, red, light green, blue, pink, and olive green colour indicates applied compressive or tensile biaxial strain of 0% (unstrained), 2%, 4%, 6%, 8%, and 10% respectively.
Fig. S4 The power factor plotted as a function of chemical potential at three different temperatures. The black, red, and blue lines indicate temperature values 300K, 500K, and 700K respectively.